

Silicon Carbide (SiC) Schottky Diode - EliteSiC, 8 A, 650 V, D2, D2PAK-2L

FFSB0865B-F085

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 33 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

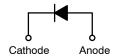
- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage	V_{RRM}	650	V	
Single Pulse Avalanche Energy ($I_{L(pk)} = 11.5 \text{ A}, L = 0.5 \text{ mH}, V = 50$	E _{AS}	33	mJ	
Continuous Rectified Forward Current	@ T _C < 147	IF	8.0	Α
Current	@ T _C < 135		10.1	
Non-Repetitive Peak Forward Surge Current	$T_C = 25^{\circ}C$ $t_P = 10 \mu s$	I _{FM}	577	Α
	$T_{C} = 150^{\circ}C$ $t_{P} = 10 \ \mu s$		533	
Non-Repetitive Forward Surge Current (Half-Sine Pulse)	$T_C = 25$ °C $t_P = 8.3$ ms	I _{FSM}	56	Α
Power Dissipation	T _C = 25°C	P _{tot}	73	W
	T _C = 150°C		12	
Operating Junction and Storage T Range	T _J , T _{stg}	-55 to +175	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

V _{RRM}	I _F	
650 V	8.0 A	

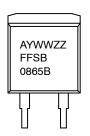


Schottky Diode



D²PAK2 (TO-263-2L) CASE 418BK

MARKING DIAGRAM



A = Assembly Plant Code YWW = Date Code (Year & Week) ZZ = Lot Code

FFSB0865B = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

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THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case, Max.	$R_{\theta JC}$	2.05	°C/W

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
ON CHARACTERISTICS			•		•	
Forward Voltage	V _F	I _F = 8.0 A, T _J = 25°C		1.39	1.7	V
		I _F = 8.0 A, T _J = 125°C		1.55	2.0	
		I _F = 8.0 A, T _J = 175°C		1.71	2.4	
Reverse Current	I _R	$V_R = 650 \text{ V}, T_J = 25^{\circ}\text{C}$		0.5	40	μΑ
		V _R = 650 V, T _J = 125°C		1.0	80	
		V _R = 650 V, T _J = 175°C		2.0	160	
CHARGES, CAPACITANCES & C	GATE RESISTANCE					
Total Capacitive Charge	$Q_{\mathbb{C}}$	V _C = 400 V		22		nC
	C _{tot}	V _R = 1 V, f = 100 kHz		336		pF
		V _R = 200 V, f = 100 kHz		39		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

 $V_R = 400 \text{ V}, f = 100 \text{ kHz}$

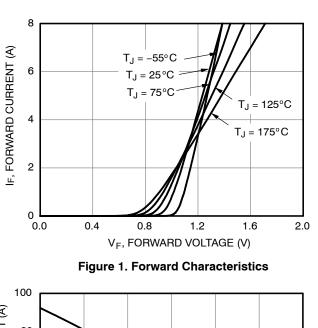
PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSB0865B-F085	FFSB0865B	D ² PAK2 (TO-263-2L)	Tape & Reel [†]	330 mm	24 mm	800 Units

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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TYPICAL CHARACTERISTICS



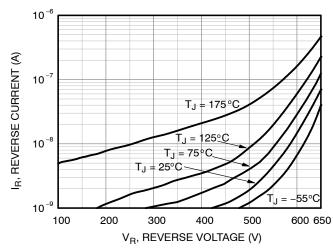
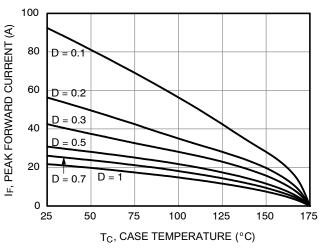


Figure 2. Reverse Characteristics



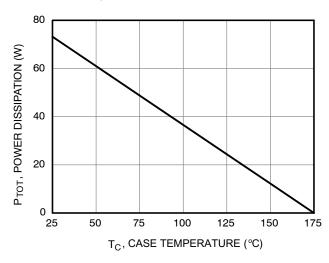
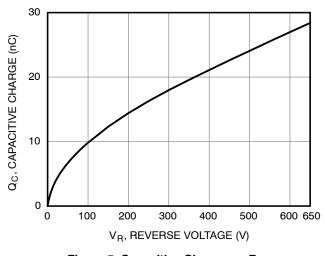


Figure 3. Current Derating

Figure 4. Power Derating



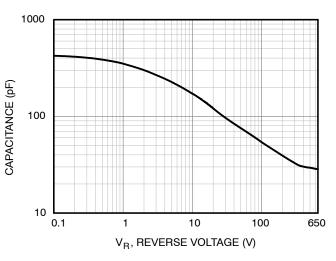


Figure 5. Capacitive Charge vs. Reverse Voltage

Figure 6. Capacitance vs. Reverse Voltage

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TYPICAL CHARACTERISTICS

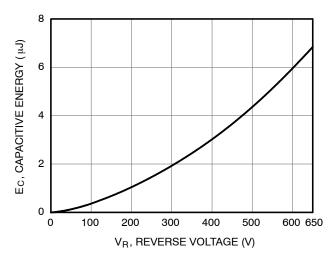


Figure 7. Capacitance Stored Energy

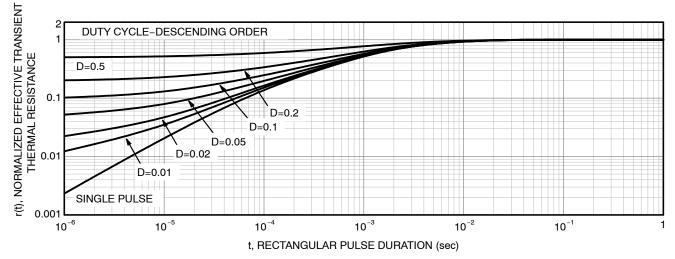
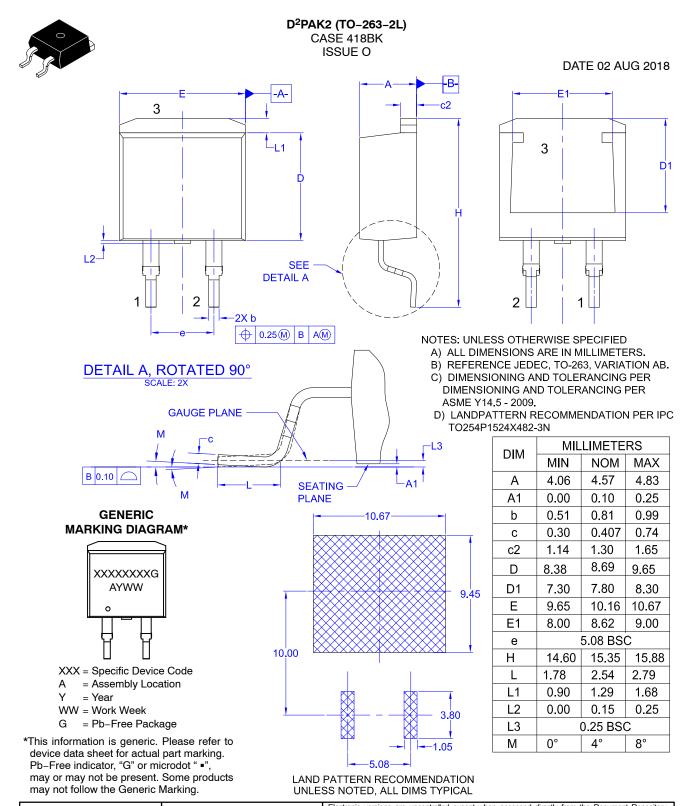


Figure 8. Junction-to-Case Transient Thermal Response



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DESCRIPTION:	D ² PAK2 (TO-263-2L)		PAGE 1 OF 1	

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